Limiting lifetimes for localized spins in GaAs

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Acknowledgements to Wei Hao (SEAP 2005) & Josh Caldwell



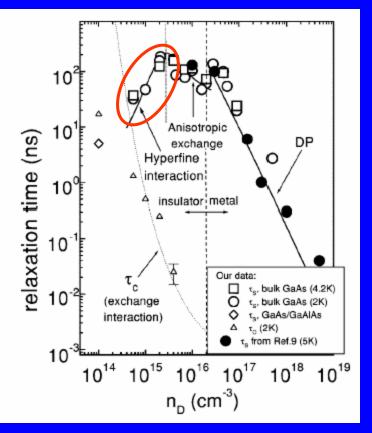
1. Background

- 1. Long lifetimes for spins in non-magnetic semiconductors
- 2. Work with donor ensembles
- 2. Magnetic resonance detected through Faraday Rotation
 - 1. Method
 - 2. Nuclear effects
 - 3. Probe light effects
 - 4. Higher concentration sample
 - 5. g-factor and Lifetime
- 3. Summary and Future Work



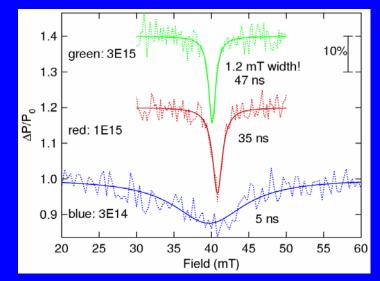
Background

- Long lifetimes in non-magnetic semiconductors
 - Kikkawa and Awschalom, PRL and Science
- Move to localized spins—qubits and quantum information
 - In III-V's—GaAs donors provide a good ensemble
 - Metal-insulator transition is at 2 X 10¹⁶ cm⁻³
 - Isolated donors for $N_D < 4 X$ 10 ¹⁴ cm⁻³ for B = 0 T

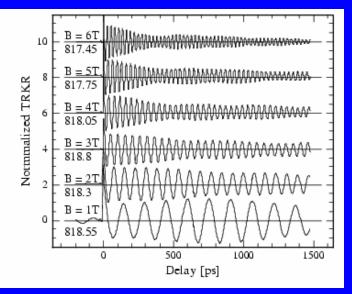


Dzhioev *et al*., Phys. Rev. B **66**, 245204 (2002)

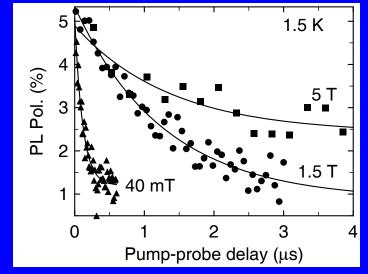
Spin lifetimes for donors in GaAs



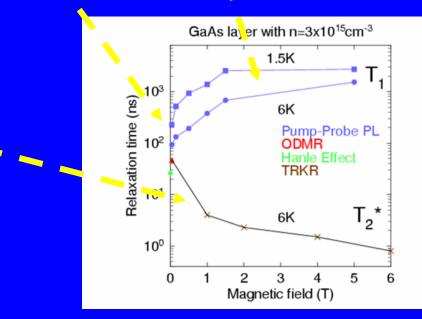
J.S. Colton et al., SSC 132, 613 (2004)



Michael Scheibner *et al.*, to be pub. NRL Electronics



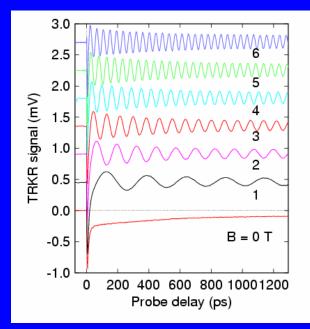
J.S. Colton *et al.*, PRB 69, 121307 (2004)



JSC: $T_1 = 24 \ \mu s$ for 1E15 at 7T

Previous work leads to

Wide Quantum Well— Simplified energy levels through HH/LH splitting



T.A. Kennedy *et al.*, PRB **73**, 045307 (2006)

Goal of Measuring T₂—Use pulsed magnetic resonance

Two challenges

- Low spin concentration
- Well defined nuclear spin state--unpolarized



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Background to This Approach

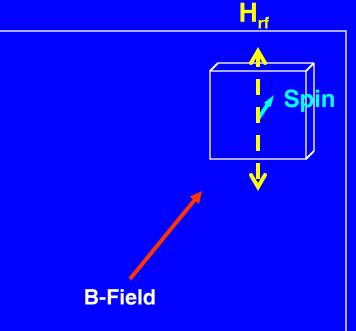
- Faraday Rotation and EPR
 - R. Romestain (1980): donors in CdS
- GaAs donors
 - Seck, Potemski and Wyder (1997): EPR—DNP enhanced
 - Karasyuk et al. (1994): Donor-bound excitons
 - Kai-Mei Fu (Stanford), Spin-flip Raman Scattering
- Nuclear Effects: ESR pinning in 2DEG's
 - Olshanetsky et al., Physica B 373, 182 (2006)
 - Hillman and Jiang, PRB 64, 201308 (2001)
 - Dobers et al., PRL 61, 1650 (1988)
- ESE in GaAs
 - Petta et al. Science **309**, 2180 (2005)—T₂ of 1 to 10 μs
 - Loss (Basel), Sham (UCSD), Whaley (UCB), Das Sarma (Maryland), ETH (Zurich), SUNY (Buffalo) and others

ODMR mechanism

off

on

- Polarization
 - Thermal: B=6 T and T=1.5 K gβH~kT
 - Off-cycle of microwaves long with respect to T₁
 - Thermalized electron spins: <S_T>
- Resonance with microwaves reduces the polarization
 - $-hv = g\beta B$
 - Frequency v = 35 GHz
 - Decreases the $\langle S \rangle$ from $\langle S_T \rangle$
- Detection...





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Detection by Kerr Rotation

+3/2

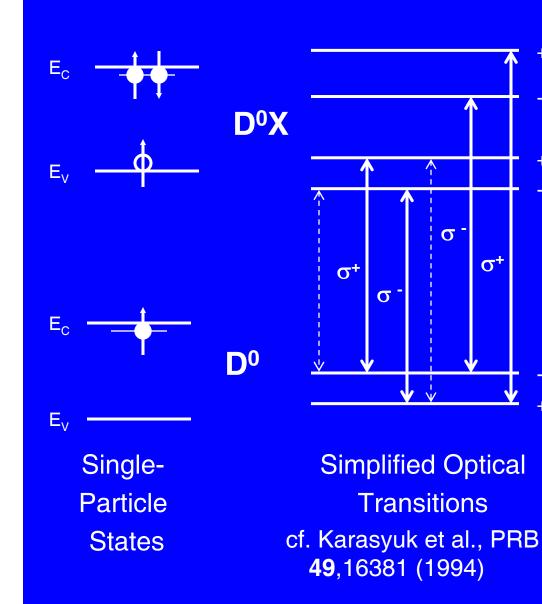
-3/2

+1/2

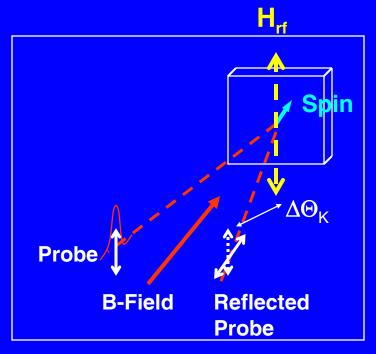
-1/2

-1/2

+1/2

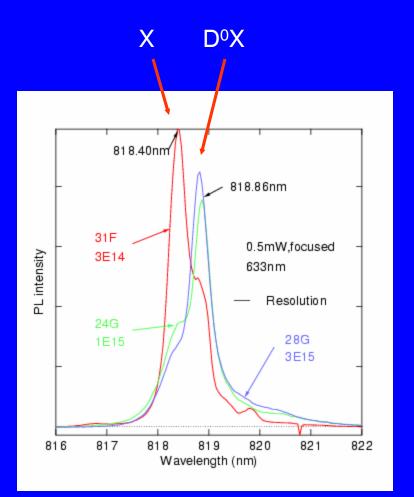


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 $\Delta \Theta = -\pi (d/\lambda)(n_+-n_-)$ (in transmission) Kerr rotation is sensitive to D⁰ spin through SOcoupling of hole in D⁰X

Experimental Details



- Samples
 - 1 µm GaAs surrounded by doped and undoped AlGaAs for flatbanding
 - Concentrations of 3E14, 1E15 and 3E15
 - (Metal-insulator transition at 2 X 10¹⁶ cm⁻³)
- Equipment
 - Oxford 7 T magnetocryostat
 - Spectra Physics ps Ti:Sa laser (∆v~1meV (0.5nm))
 - Agilent 250kHz to 40GHz signal generator



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Nuclear Spin Effects

1. Without nuclei, the Bloch equations describe the saturation of the ESR amplitude (A) with microwave power (P):

 $\mathsf{A} = (\alpha \mathsf{P}) / (\mathsf{1} + \beta \mathsf{P})$

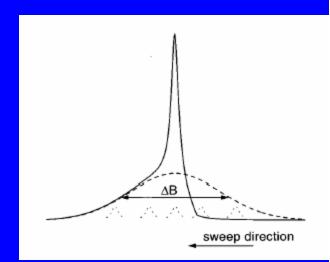
- With nuclei, Dynamic Nuclear Polarization arises from the Overhauser effect: Saturated e-spins try to relax through the nuclear spins using the (I⁺S⁻ + I⁻S⁺) part of the hyperfine interaction
- 3. Sign of the nuclear field: B_N adds to the external field (B_{ext})

a. $\langle I \rangle = [I(I + 1)/S(S+1)] * [\langle S \rangle - \langle S_T \rangle] < 0$

b.
$$B_N = A < I > / g_e \beta ; g_e < 0; B_N > 0$$

c. $hv = g\beta (B_{ext} + B_N)$

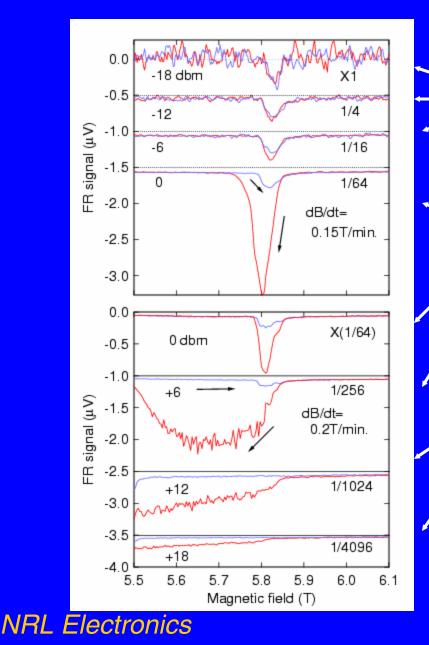
- 4. Enhancement and pinning of the ESR can occur:
 - a. Compare dB_N/dt with dB_{ext}/dt
 - b. DNP \propto P
 - c. Nuclear relaxation time ~ 1 minute
 - d. Strong effects occur for downward field sweeps



Seck et al., 1997 *March 2006*

NRL Electronics Olshanetsky et al., Physica B 373, 182 (2006)

Dependence on Microwave Power



 $dB_N/dt \propto Saturation \propto P$

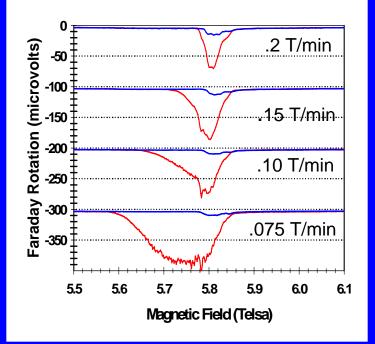
- Unsaturated limit
 - Down & up are the same
 - Amplitude ∞ power

DNP enhanced: $dB_N/dt \approx |-dB_{ext}/dt|$

- Strong for down sweeps
- Broadened & shifted
- Up sweeps unaffected
- ESR pinning: dB_N/dt > | -dB_{ext}/dt |
 - Resonance not achieved
 - B_N becomes > 0.3 T

817.8 nm (near res.), 9/20 &9/19 data, 31F, T = 1.5 K, 35 GHz

Dependence on Rate of Change of External Magnetic Field



• 0 dbm, 9/17/05, 817.8 nm

- Dyanamics is again controlled by the relative size of dB_N/dt and -dB_{ext}/dt
- Rate of DNP induced B_N is constant since microwave power (P) is constant.
- Decreasing the sweep rate of magnetic field (-dB_{ext}/dt) changes the response from DNP enhanced to ESR pinning.

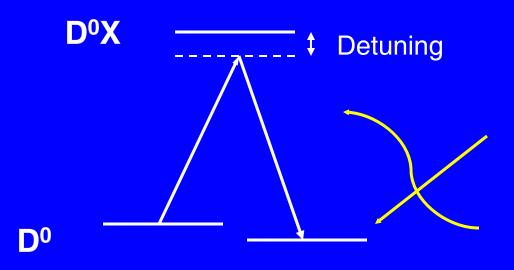
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Effects of the Probe Light



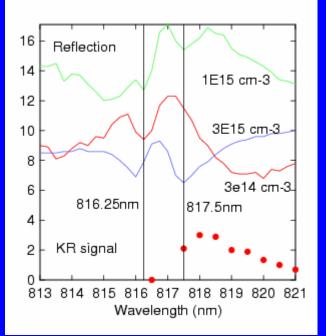
The experiment is a double resonance

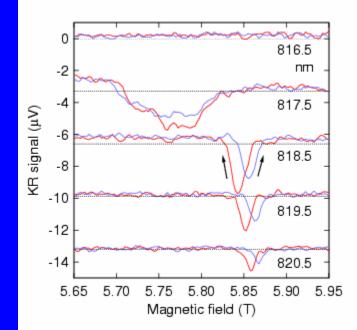
- Microwave resonance in the ground state—tuned by changing the magnetic field
- Optical resonance to the excited state—tuned by changing the laser wavelength





Dependence on Wavelength of the Probe Light





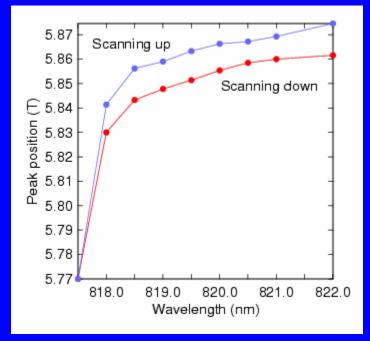
- Optical Resonances for B = 6T
 - D⁰X at 817.5 nm
 - X at 816.25 nm

-6dbm, 34.694, 300 uW probe, 9/20/05 data

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- On resonance
 - Large shift
 - Extra line
- Detuned to lower E (longer λ)
 - Sharp single line
 - Decreasing amplitude
 - Slow shift

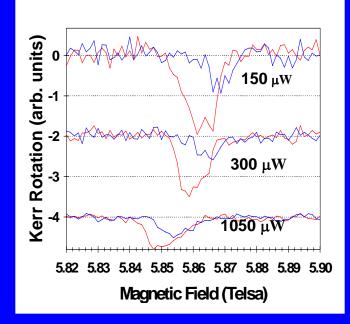
Peak Position versus probe wavelength and power



Position versus wavelength

 Approaches a limit offresonance

9/20/05 data—31F, light unfocussed NRL Electronics



Position versus power

- Shifts to lower fields with increasing power
- DNP by slight depolarization of <S> by the linearly polarized light

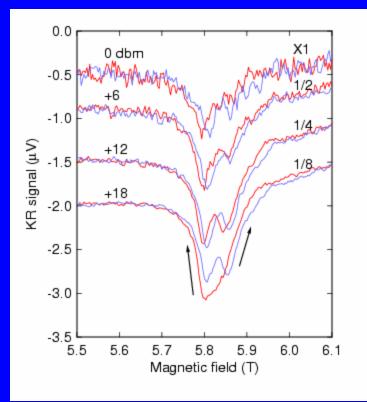
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9/21/05 data, 820.5nm,-6dbm
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Dependence on Microwave Power for 3E15



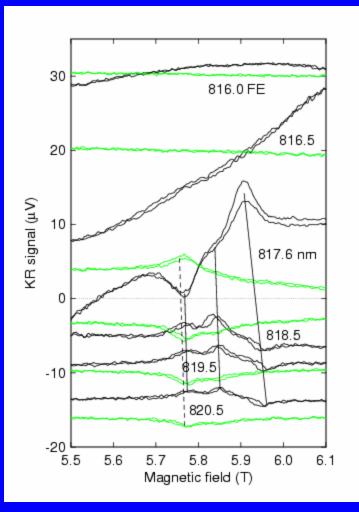
28G, 818.6nm, 8/9/05, no offset added



- Two lines
- Strong signals in quadrature
- DNP enhanced for high-field line at highest power
- Localized and delocalized electrons

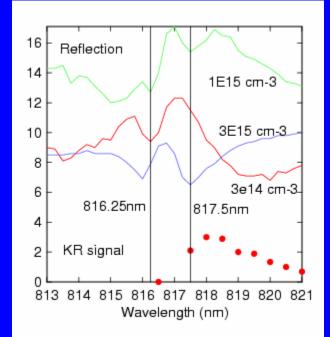
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Dependence on wavelength of probe



24 G, 3E15, 8/11/05, +6dbm,0.15 T/min

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- Black: in phase; Green: in quadrature
- In Phase
 - 2 or 3 resonances
 - phase changes
- In Quadrature
 - one resonance
 - reveals dynamics ~ 3 khzrch 2006

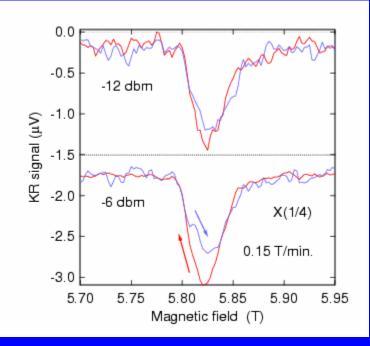
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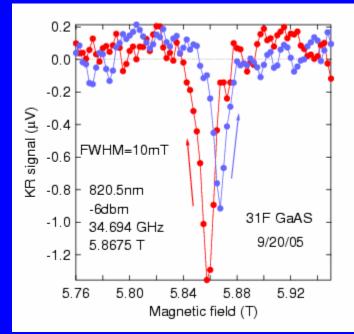
- 1. Long lifetimes for spins in non-magnetic semiconductors
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g-factor and linewidth





Near resonance—817.8 nm

- g = 0.431; FWHM = 49 mT
- Real transitions
 - D⁰X: holes
 - X: electrons and holes

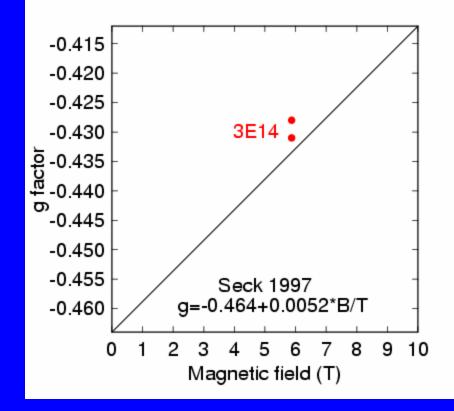
Off resonance—820.5 nm

- g = 0.428; FWHM = 10 mT
- Dispersive part of the index

Sweep rate 0.15 T/min

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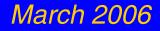
Comparison of g-factors with other work



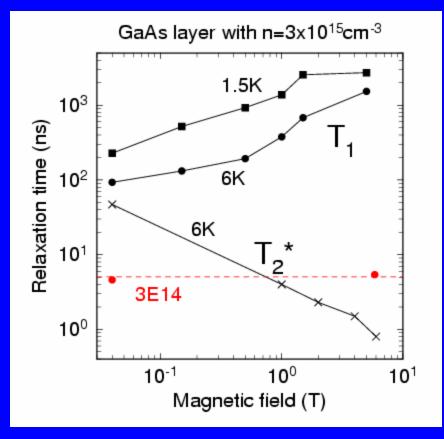
• Negative sign added

• 31F shown for near resonance & off-resonance





T_2^* for donors in GaAs



- ~5 ns for low and high magnetic fields
- Limited by fluctuation in nuclear spin
- Good starting point for measuring T₂

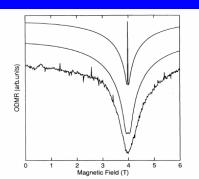




Lifetimes for donors at high magnetic fields

	Sample	∆B FWHM (mT)	T ₂ *
This work	$N_{D}-N_{A} =$ 3X10 ¹⁴ cm ⁻³	10	5.4 ns
Kai-Mei Fu et al. (06)	N _D -N _A = 5X10 ¹³ cm ⁻³		2.3 ns
Seck et al. (1997)	$N_{\rm D}$ - $N_{\rm A}$ = 6.6X10 ¹⁴ cm ⁻³	50	1.1 ns
Kikkawa & Awschalom (1998)	Semi- insulating		100 ps
Trombetta & Kennedy (1993)	Semi- insulating	900	60 ps

g-broadening is small, possibly negligible



Summary and Future Work

- Kerr rotation provides adequate sensitivity to work with isolated donors
- Nuclear effects
 - Resonance without DNP enhancement –unpolarized nuclei
 - DNP enhancement—good for finding ESR
 - ESR-pinning—possibly good for polarizing nuclei
- Linewidth near or at the hyperfine limit—little or no gbroadening

• Measuring T₂ with electron-spin-echo in ensembles

